

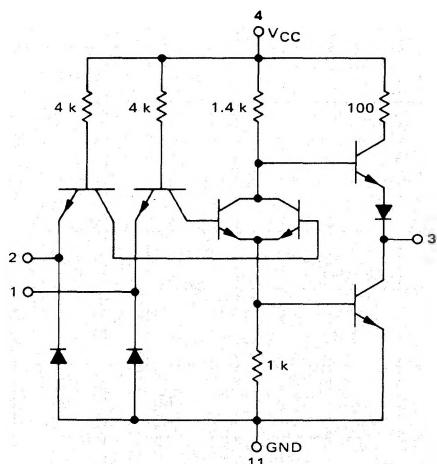
QUAD 2-INPUT "NOR" GATE

MCBC5400/MCB5400F series

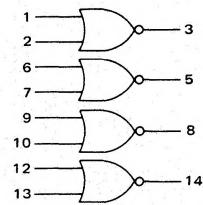
MCBC5402* MCB5402F*



1/4 OF CIRCUIT SHOWN



This device consists of four 2-input NOR gates that is produced using beam lead sealed junction technology. These devices are particularly useful in highly reliable systems using hybrid beam lead assembly techniques or standard flat package assembly techniques.



Positive Logic: $3 = \overline{1 + 2}$

Negative Logic: $3 = \overline{1} \cdot \overline{2}$

Input Loading Factor = 1

Output Loading Factor = 10

Total Power Dissipation = 48 mW typ/pkg

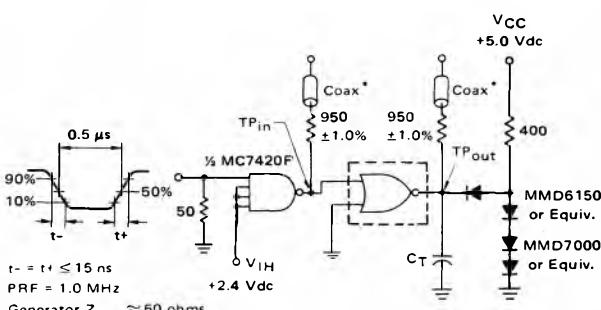
Propagation Delay Time = 10 ns typ

Package No.	1	2	3	4	5	6	7	8	9	10	11	12	13	14
Beam No.	1	2	3	4	5	6	7	9	10	11	12	13	14	15

Pin numbers on drawings are for devices in the flat package.

VOLTAGE WAVEFORMS AND DEFINITIONS

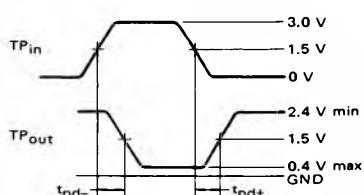
SWITCHING TIME TEST CIRCUIT



$t^- = t^+ \leq 15$ ns
PRF = 1.0 MHz
Generator $Z_{out} \approx 50$ ohms

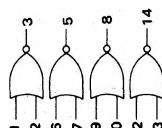
$C_T = 15$ pF = total parasitic capacitance, which includes probe, wiring, and load capacitances.

*The coax delays from input to scope and output to scope must be matched. The scope must be terminated in 50-ohm impedance. The 950-ohm resistor and the scope termination impedance constitute a 20:1 attenuator probe. Coax shall be CT-070-50 or equivalent.



ELECTRICAL CHARACTERISTICS

Test procedures are shown for only one gate. The other gates are tested in the same manner. Further, test procedures are shown for only one input of the gate under test. To complete testing, sequence through remaining inputs. Pin numbers used are for devices in the flat package.



MCBC5402, MCB5402F (continued)

TEST CURRENT/VOLTAGE VALUES (All Temperatures)																					
Characteristic	Symbol	Pin Under Test	Min	Max	Unit	I _{OL}	I _{OH}	V _{IL}	V _{IH}	V _{IHH}	V _{R1}	V _{R2}	V _{H1}	V _{H2}	V _{Hh1}	V _{Hh2}	V _{CC}	V _{CC1}	V _{CC2}	V _{CCH}	Gnd
TEST CURRENT/VOLTAGE APPLIED TO PINS LISTED BELOW:																					
Input Forward Current	I _F	1	-	-1.6	mAdc	-	-	1	-	-	2	-	-	-	-	-	-	-	4	11*	
Leakage Current	I _{R1}	1	-	40	μAdc	-	-	1	-	-	-	-	-	-	-	-	-	-	4	2,11*	
	I _{R2}	1	-	1.0	mAdc	-	-	-	-	1	-	-	-	-	-	-	-	-	4	2,11*	
Output Output Voltage	V _{OL}	3	-	0.4	Vdc	3	-	-	-	-	-	-	-	1	-	-	4	-	2,11*		
	V _{OH}	3	2.4	-	Vdc	-	3	-	-	-	-	-	-	-	2	-	4	-	1,11*		
Short-Circuit Current	I _{SC}	3	-20	-55	mAdc	-	-	-	-	-	-	-	-	-	-	-	-	-	4	1,2,3,11*	
Power Requirements (Total Device) Power Supply Drain																					
	I _{PDH}	4	-	27	mAdc	-	-	-	-	-	-	-	-	1,2,6,7,9, 10,12,13	-	-	-	-	4	11	
Switching Parameters	I _{PDL}	4	-	16	mAdc	-	-	-	-	-	-	-	-	-	-	-	-	-	4	1,2,11*	
Turn-On Delay	t _{pd+}	1,3	-	15**	ns	1	3	-	-	-	-	-	-	-	-	-	-	-	4	-	2,11*
Turn-Off Delay	t _{pd+}	1,3	-	22**	ns	1	3	-	-	-	-	-	-	-	-	-	-	-	4	-	2,11*

*Ground inputs to gates not under test.
**Tested only at 25°C.